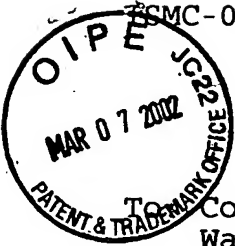


SMC-01-450



3 / IDS 2825  
ع. ب. أكerman  
10-29-03

February 22, 2002

Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572  
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Subject:

Serial No. 10/042,074 01/08/02

Dun-Nian Young et al.

GRID METAL DESIGN FOR LARGE DENSITY  
CMOS IMAGE SENSOR

Grp. Art Unit: 2825

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56. Copies of each document is included herewith.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
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Trademarks, Washington, D.C. 20231, on February 27, 2002.

Stephen B. Ackerman, Reg.# 37761

Signature/Date Stephen B. Ackerman 2/27/02

U.S. Patent 5,278,105 to Eden et al., "Semiconductor Device with Dummy Features in Active Layers," discloses a method in which dummy features are introduced to increase the percentage of material remaining after etch and thereby to reduce the loading affect.

U.S. Patent 5,798,298 to Yang et al., "Method of Automatically Generating Dummy Metals for Multilevel Interconnection," discloses using dummy metal shaped in blocks to prevent the loading affect during etching for multilevel interconnection.

U.S. Patent 5,915,201 to Chang et al., "Trench Surrounded Metal Pattern," discusses dummy metal areas with sizes similar to the functional metal lines distributed among the functional lines reducing the loading affect.

U.S. Patent 5,926,733 to Heo, "Metal Layer Patterns of a Semiconductor Device and a Method for Forming the Same," discusses using dummy metal patterns to reduce loading affects.

U.S. Patent 6,180,448 to Lee, "Semiconductor Memory Device Having a Capacitor Over Bitline Structure and Method for Manufacturing the Same," discusses using dummy storage electrodes to alleviate the loading affect.

Sincerely,

  
Stephen B. Ackerman, Reg. #37761

Form PTO-1449

Sheet 1 of 1

INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)

TSMC-01-450

Application Number

10/042,074

Applicant

Dun-Nian Young et al.

Filing Date

01/08/02

Group XVI Unit

2825

## U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	PLUNG DATE IF APPROPRIATE
	5278105	1/11/94	Eden et al.	437	250	8/19/92
	5798298	8/25/98	Yang et al.	438	622	2/9/96
	5915201	6/22/99	Chang et al.	438	631	10/30/97
	5926733	7/20/99	Heo	438	622	4/2/97
	6180448	1/30/01	Lee	438	253	9/17/98



## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)


EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.